

UNISONIC TECHNOLOGIES CO., LTD

T2096

NPN SILICON TRANSISTOR

TO-251

TO-252

HIGH VOLTAGE TRANSISTOR

DESCRIPTION

The T2096 is a NPN Silicon Planar Transistors in TO-251 package. It is intended for high voltage, switching power supply and industrial applications.

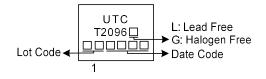
FEATURES

- * Pb-free package is available
- * Collector-Emitter voltage: V_{CEO} = 400V
- * Pulse collector current to 4A

ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Dealing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
T2096L-TM3-T	2096L-TM3-T T2096G-TM3-T		В	С	Е	Tube	
T2096L-TN3-R	T2096G-TN3-R TO-252 B		С	Е	Tape Reel		
Note: Pin Assignment: E: Emitter C: Collector B: Base							
T2096G-TM3-T (1)Packing Type (2)Package Type (3)Green Package		 (1) T: Tube, R: Tape Reel (2) TM3: TO-251, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free 					

MARKING



■ **ABSOLUATE MAXIUM RATINGS** (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage		V _{CBO}	800	V	
Collector-Emitter Voltage		V _{CES}	800	V	
Collector-Emitter Voltage		V _{CEO}	400	V	
Emitter-Base Voltage		V _{EBO}	8	V	
Base Current		I _B	1	A	
DC Collector Current		lc	2	A	
Pulse Collector Current (Note 2)		I _{CP}	4	A	
	=25°C		1	W	
Collector Dissipation T _C :	=25°C	Pc	15	W	
unction Temperature		TJ	150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Notes: 1.Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Pulse Test: Pulse Width \leq 300µS, Duty Cycle \leq 10%.

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-251	0		°C/W
	TO-252	θ _{JA}	125 (Note)	°C/W
Junction to Case	TO-251	θ _{JC}		°C/W
	TO-252		8.33 (Note)	°C/W

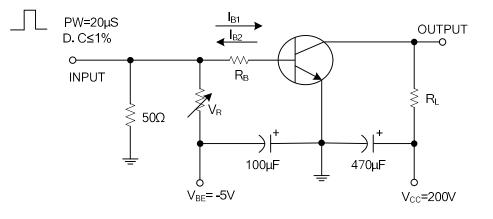
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =1mA, I _E =0	800			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =5mA, R _{BE} =∞	400			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =1mA, I _C =0	8			V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =1A, I _B =0.2A			0.8	V
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =1A, I _B =0.2A			1.5	V
Collector Cutoff Current	I _{CBO}	V _{CB} =400V, I _E =0			10	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0			10	μA
DC Current Cain	h _{FE 1}	V _{CE} =5V, I _C =1mA	45			
DC Current Gain	h _{FE 2}	V _{CE} =5V, I _C =0.2A	120		180	
Current Gain-Bandwidth Product	f⊤	V _{CE} =10V, I _C =0.2A		20		MHz
Output Capacitance	Cob	V _{CB} =10V, f =1MHz		20		рF
Turn-on Time	t _{on}	I _C =1.0A, I _{B1} =0.05A			0.5	μs
Storage Time	t _{stg}	I _{B2} = -0.5A, R _L =200Ω			2.5	μs
Fall Time	t _F	V _{CC} =200V			0.3	μs

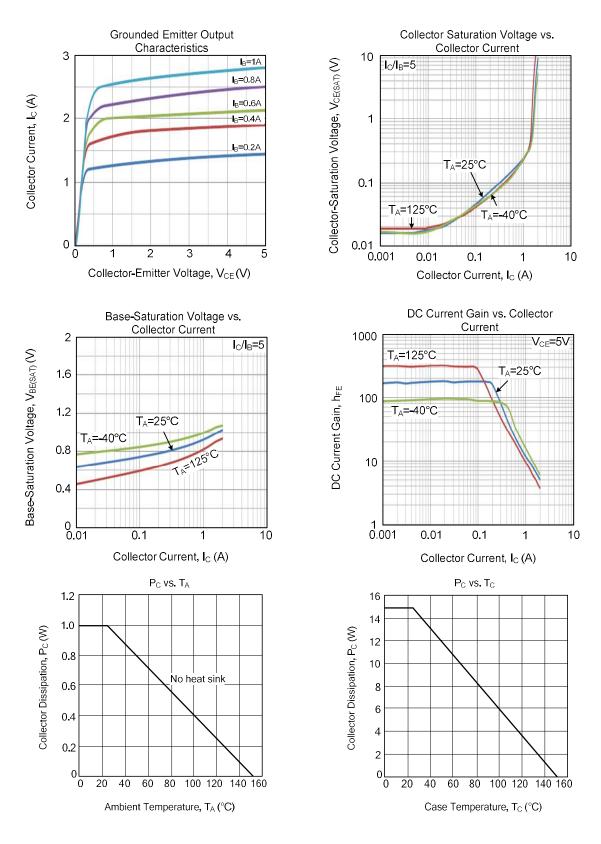


SWITCHING TIME TEST CIRCUIT



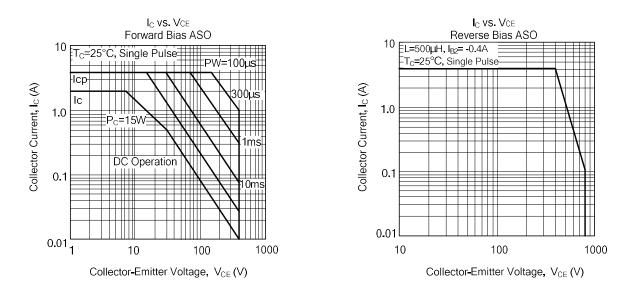


TYPICAL CHARACTERISTICS





■ TYPICAL CHARACTERISTICS



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